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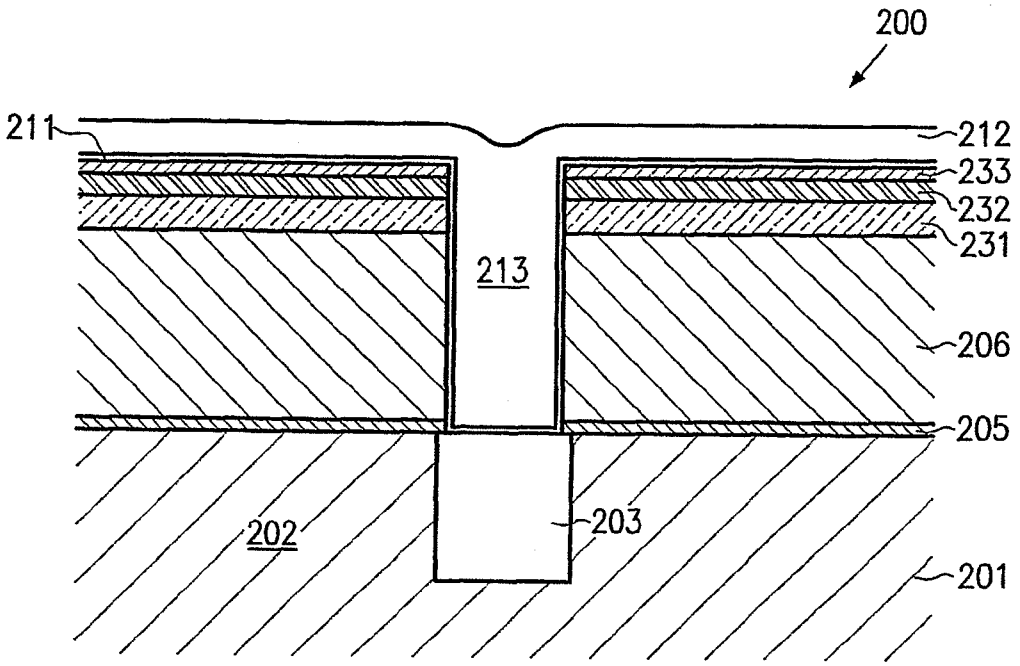
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(54) Title: METHOD OF FORMING A CAP LAYER HAVING ANTI-REFLECTIVE CHARACTERISTICS ON TOP OF A LOW-K DIELECTRIC



(57) Abstract: A method of forming a multi-layer stack (230) over a low-k dielectric layer (206) is disclosed, wherein the multi-layer stack (230) provides an improved anti-reflective effect and an enhanced protection of the underlying low-k dielectric material during the chemical mechanical polishing process. The multi-layer stack (230) comprises silicon dioxide based sub-layers (231, 232, 233), which may be formed in a highly efficient, non-expensive plasma enhanced deposition method, wherein the optical characteristics may be adjusted by varying a ratio of silane and nitrogen oxide during the deposition.

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